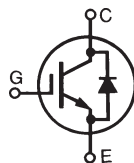


High Voltage, High Gain BIMOSFET™ Monolithic Bipolar MOS Transistor

IXBT22N300HV IXBH22N300HV



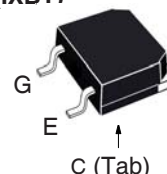
$$V_{CES} = 3000V$$

$$I_{C110} = 22A$$

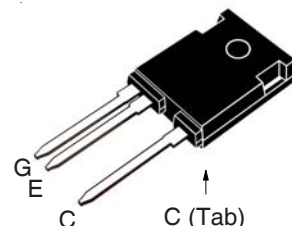
$$V_{CE(sat)} \leq 2.7V$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	3000	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	3000	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	60	A
I_{C110}	$T_C = 110^\circ C$	22	A
I_{CM}	$T_C = 25^\circ C$, 1ms	190	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 15\Omega$ Clamped Inductive Load	$I_{CM} = 180$	A
		$V_{CES} \leq 1500$	V
T_{SC} (SCSOA)	$V_{GE} = 15V$, $T_J = 125^\circ C$, $R_G = 52\Omega$, $V_{CE} = 1500V$, Non-Repetitive	10	μs
P_C	$T_C = 25^\circ C$	290	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
M_d	Mounting Torque (TO-247HV)	1.13/10	Nm/lb.in
Weight	TO-268HV	4	g
	TO-247HV	6	g

TO-268HV (IXBT)



TO-247HV (IXBH)



G = Gate C = Collector
E = Emitter Tab = Collector

Features

- High Voltage Packages
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage

Advantages

- Low Gate Drive Requirement
- High Power Density

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

Symbol	Test Conditions ($T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	3000		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			25 μA 1.5 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 22A$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$		2.2 2.7	V V

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max.
g_{fs}	$I_C = 22\text{A}, V_{CE} = 10\text{V}$, Note 1	13	22	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		2200	pF
C_{oes}			85	pF
C_{res}			30	pF
$Q_{g(on)}$	$I_C = 22\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1500\text{V}$		110	nC
Q_{ge}			13	nC
Q_{gc}			45	nC
$t_{d(on)}$	Resistive Switching Times, $T_J = 25^\circ\text{C}$		46	ns
t_r			360	ns
$t_{d(off)}$			205	ns
t_f			1820	ns
$t_{d(on)}$	Resistive Switching Times, $T_J = 125^\circ\text{C}$		43	ns
t_r			700	ns
$t_{d(off)}$			220	ns
t_f			1650	ns
R_{thJC}				0.43 $^\circ\text{C/W}$
R_{thCS}	TO-247HV		0.21	$^\circ\text{C/W}$

Reverse Diode

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max
V_F	$I_F = 22\text{A}, V_{GE} = 0\text{V}$, Note 1			2.7 V
t_{rr}	$I_F = 11\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$		1.4	μs
I_{RM}			30	A
Q_{RM}			21	μC

Note: 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

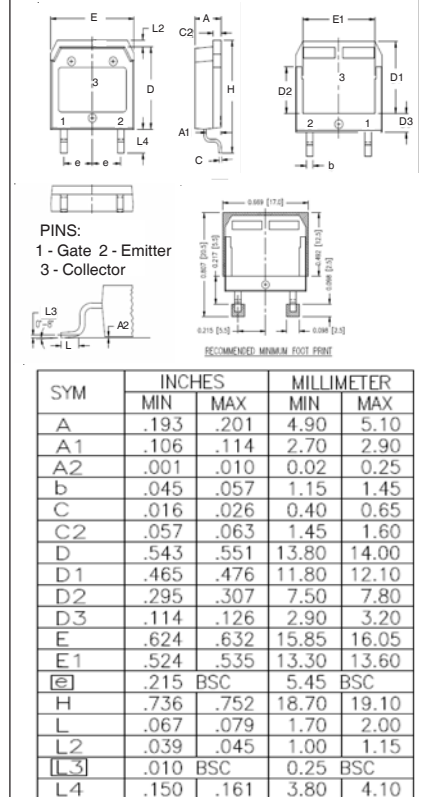
ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

TO-268HV Outline



TO-247HV Outline

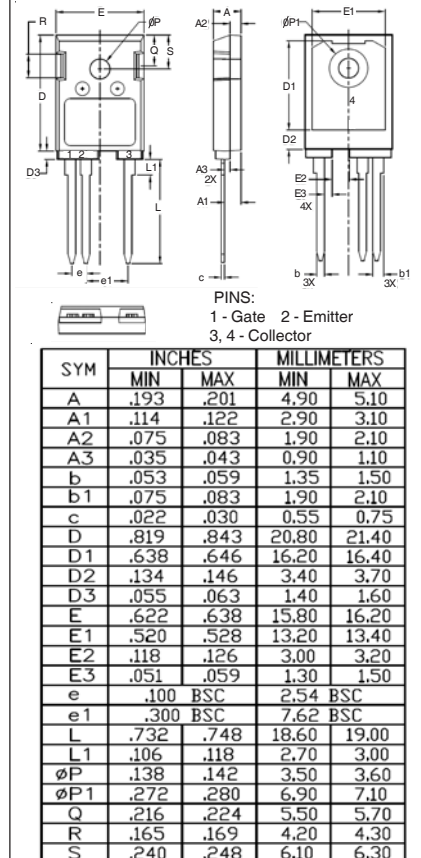


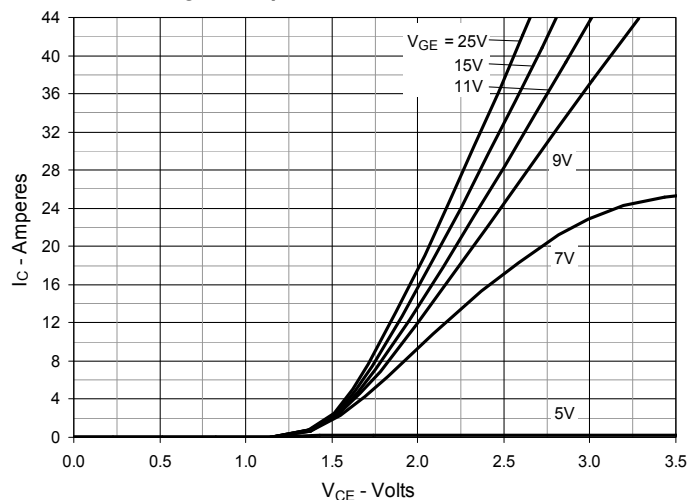
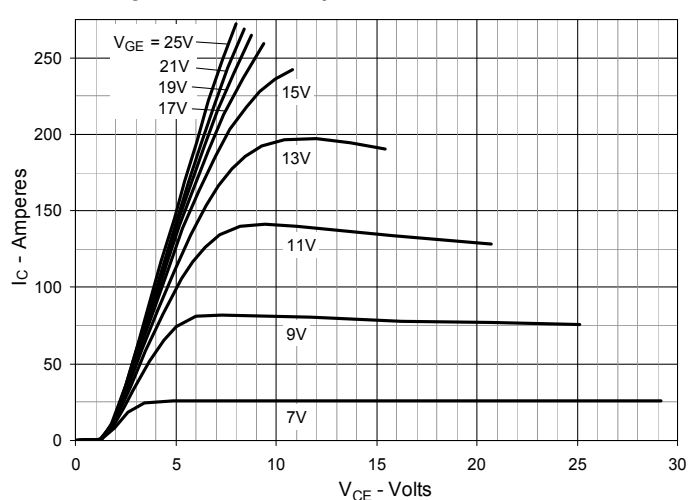
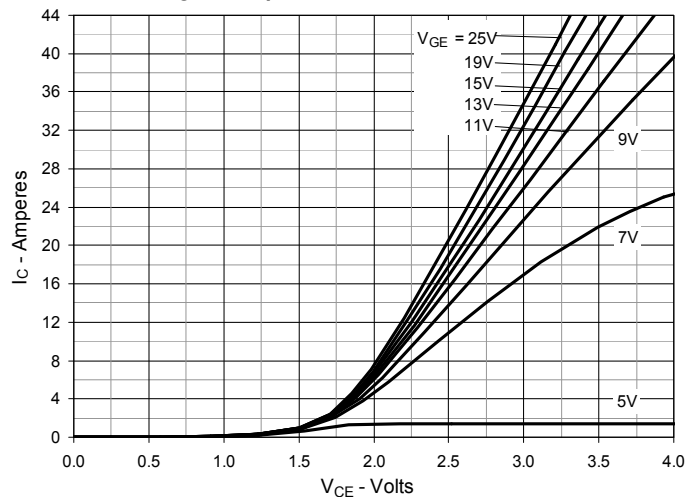
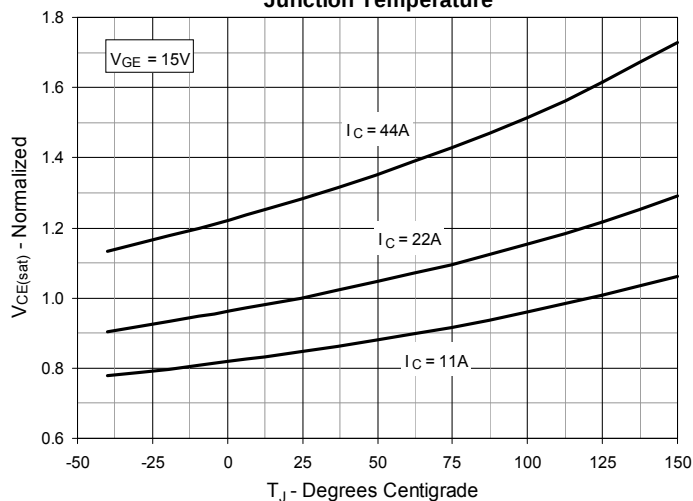
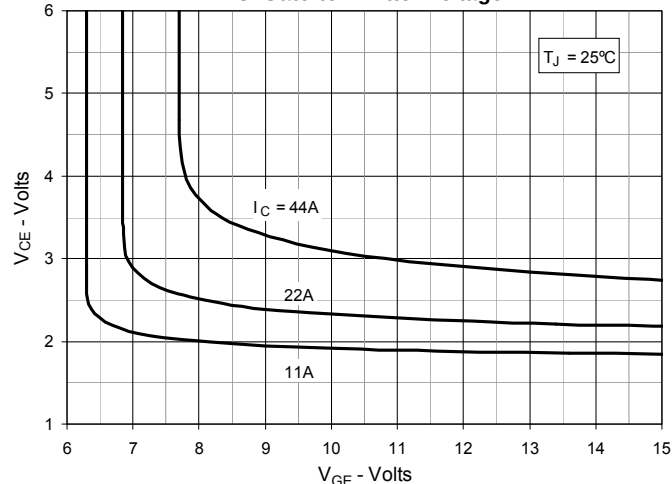
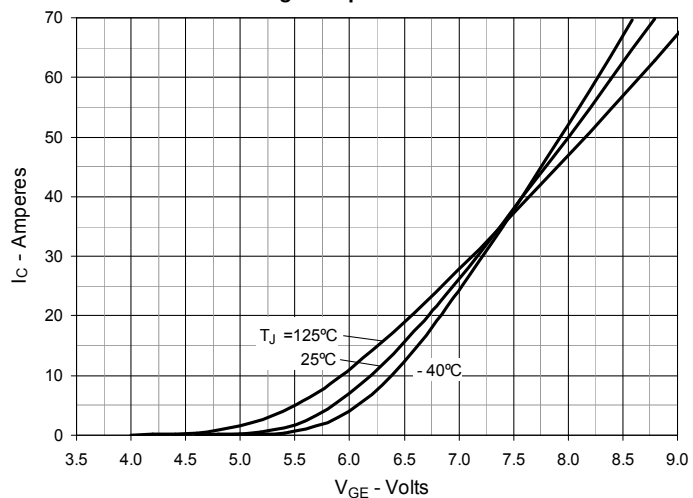
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


Fig. 7. Transconductance

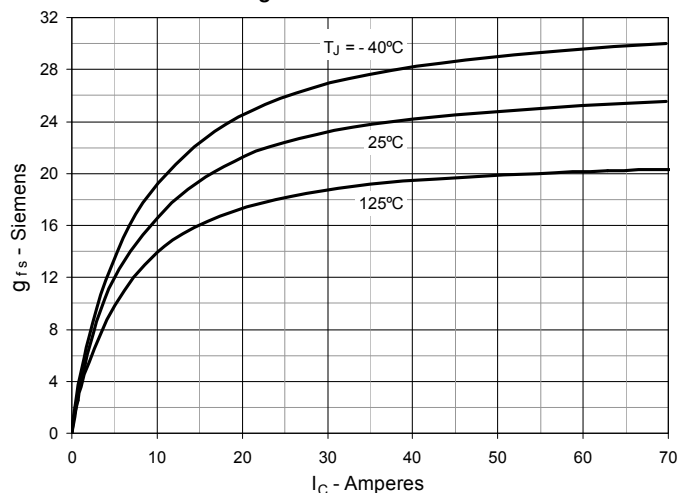


Fig. 8. Gate Charge

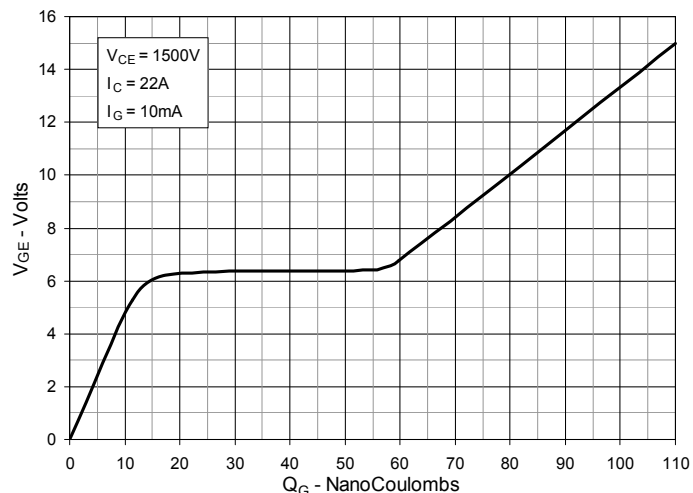


Fig. 9. Forward Voltage Drop of Intrinsic Diode

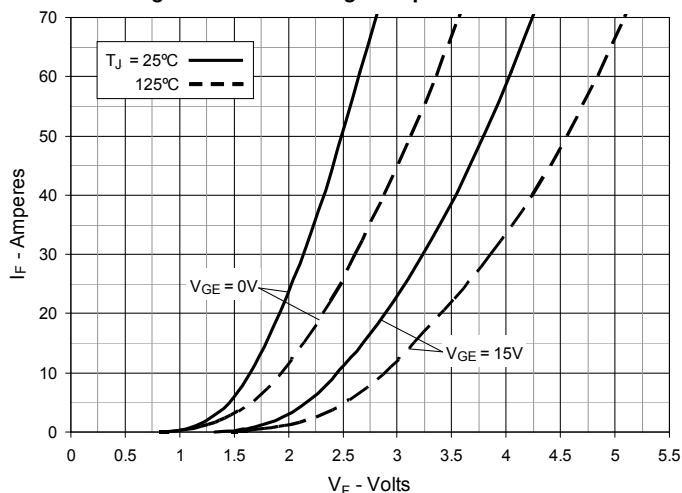


Fig. 10. Capacitance

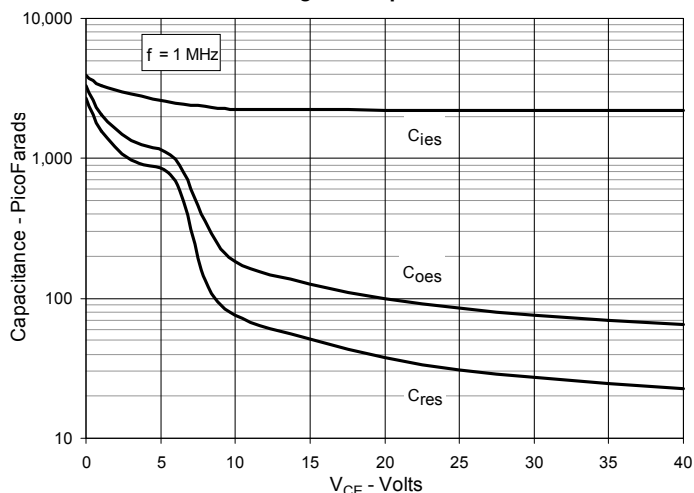


Fig. 11. Reverse-Bias Safe Operating Area

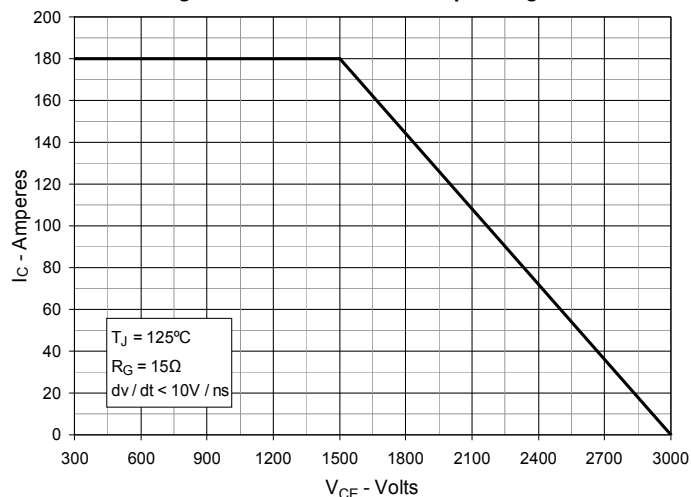


Fig. 12. Maximum Transient Thermal Impedance

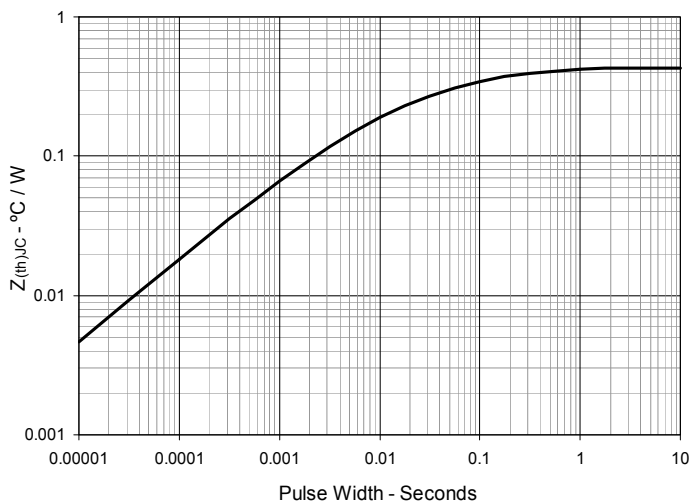


Fig. 13. Forward-Bias Safe Operating Area @ $T_C = 25^\circ\text{C}$

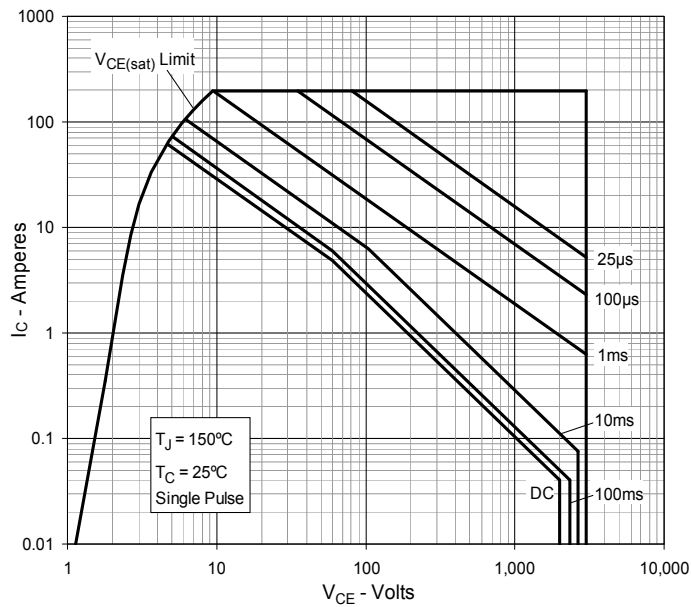
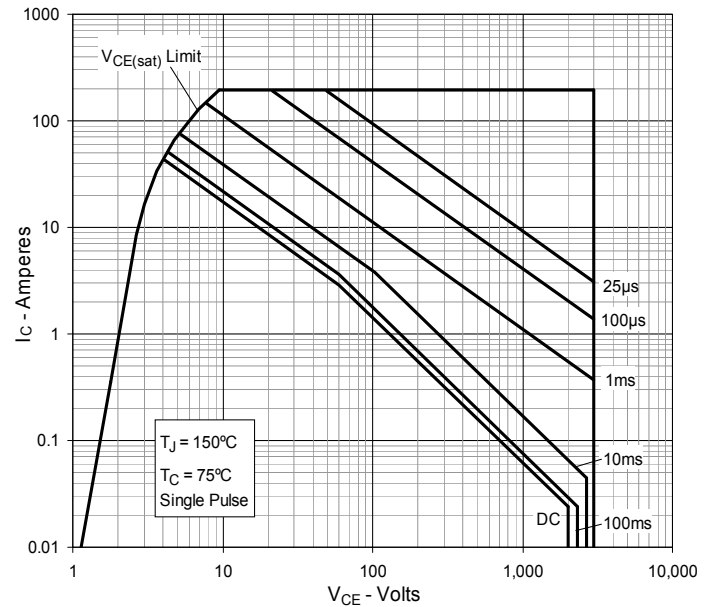


Fig. 14. Forward-Bias Safe Operating Area @ $T_C = 75^\circ\text{C}$





Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.